



PTO/SB/06a/b (08-03)

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| Substitute for form 1449A/B/PTO | | | | Complete if Known | |
| | | | | Application Number | 10/721,488 |
| INFORMATION DISCLOSURE STATEMENT BY APPLICANT (Use as many sheets as necessary) | | | | Filing Date | November 25, 2003 |
| | | | | First Named Inventor | Shiping Guo |
| | | | | Art Unit | 2844 2826 |
| | | | | Examiner Name | Net-Yet-Assigned Minh-Luan Tran |
| Sheet | 1 | of | 1 | Attorney Docket Number | EMCORE 3.0-081 |

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| Examiner Initials* | Cite No. ¹ | Document Number | Publication Date MM-DD-YYYY | Name of Patentee or Applicant of Cited Document | Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear |
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| Examiner Signature | Minh Luan Tran | Date Considered | 8/05 |
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**INFORMATION DISCLOSURE
STATEMENT BY APPLICANT**

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| Art Unit | N/A- 2826 |
| Examiner Name | Not Yet Assigned- Minhloan Tran |
| Attorney Docket Number | EMCORE 3.0-081 |

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| Sheet | 1 | of | 2 |
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| Sheet | 2 | of | 2 | Attorney Docket Number | EMCORE 3.0-081 |

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